

NTBLS002N08MC

MOSFET - Power, Single N-Channel, TOLL 80 V, 2 mΩ, 238 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Lowers Switching Noise/EMI
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	80	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	I_D	238	A
			P_D	208	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	28	A
			P_D	2.9	W
Pulsed Drain Current	$T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	3523	A	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	$^\circ\text{C}$	
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 28 \text{ A}, L = 3 \text{ mH}$)		E_{AS}	1176	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State (Note 2)	$R_{\theta JC}$	0.6	$^\circ\text{C/W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	43	

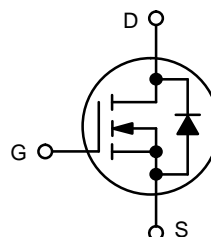
1. Surface-mounted on FR4 board using a 1 in² pad size, 1 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.



ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
80 V	2 mΩ @ 10 V	238 A
	5 mΩ @ 6 V	

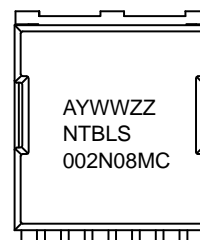


N-CHANNEL MOSFET



M0-299A
TOLL
CASE 100CU

MARKING DIAGRAM



NTBLS002N08MC = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NTBLS002N08MC

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		64		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 530\ \mu\text{A}$	2.0	3.0	4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 530\ \mu\text{A}$, ref to 25°C		-8.5		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 80\text{ A}$		1.7	2.0	m Ω
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 6\text{ V}, I_D = 47\text{ A}$		2.8	5.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 80\text{ A}$		186		S
Gate Resistance	R_G	$T_A = 25^\circ\text{C}$		0.4		Ω

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 40\text{ V}$		6580		pF
Output Capacitance	C_{OSS}			1950		
Reverse Transfer Capacitance	C_{RSS}			74		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}; I_D = 80\text{ A}$		92		nC
Threshold Gate Charge	$Q_{G(TH)}$			19		
Gate-to-Source Charge	Q_{GS}			30		
Gate-to-Drain Charge	Q_{GD}			21		
Output Charge	Q_{OSS}			123		
Sync Charge	Q_{sync}			81		
Plateau Voltage	$V_{plateau}$			5		V

SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{ V}$ (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}, I_D = 80\text{ A}, R_G = 6\ \Omega$		34		ns
Rise Time	t_r			30		
Turn-Off Delay Time	$t_{d(OFF)}$			62		
Fall Time	t_f			24		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 2\text{ A}$		0.7	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 80\text{ A}$		0.8	1.3	
Reverse Recovery Time	t_{RR}	$I_F = 40\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		35		nS
Reverse Recovery Charge	Q_{RR}			74		nC
Reverse Recovery Time	t_{RR}	$I_F = 40\text{ A}, di/dt = 1000\text{ A}/\mu\text{s}$		27		nS
Reverse Recovery Charge	Q_{RR}			166		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

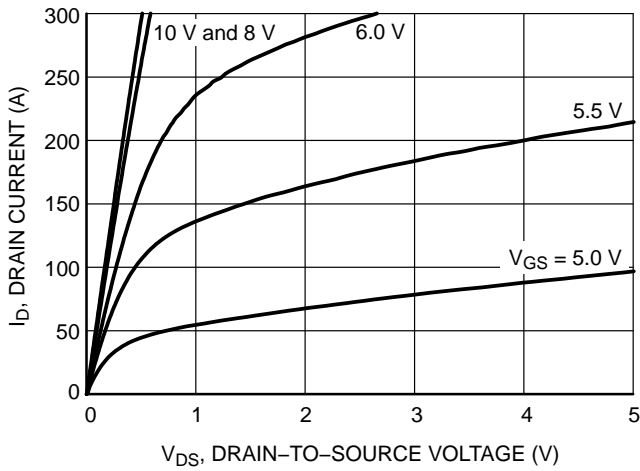


Figure 1. On-Region Characteristics

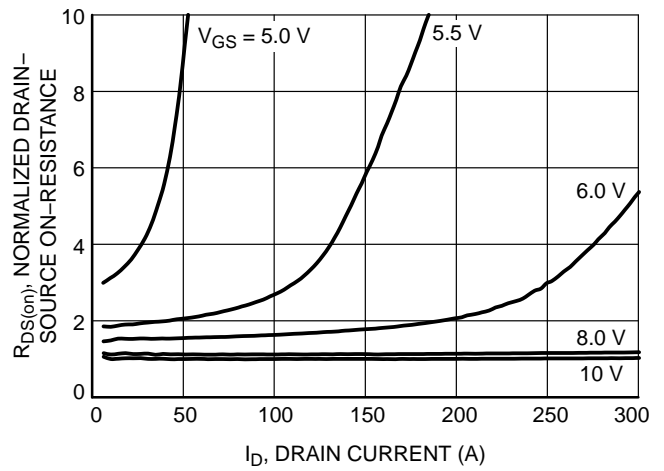


Figure 2. $R_{DS(on)}$ Normalized vs. I_D

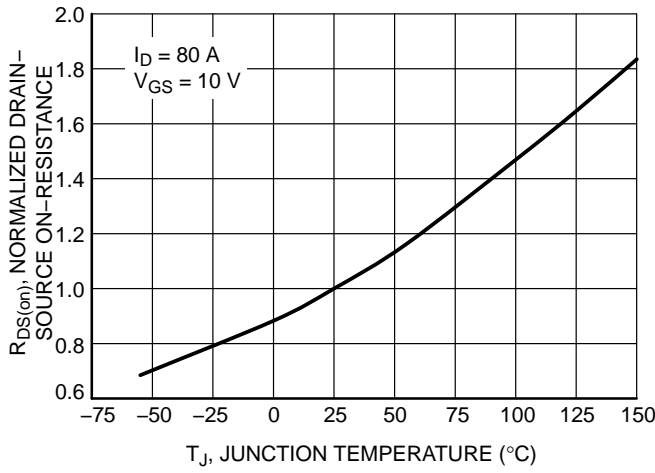


Figure 3. $R_{DS(on)}$ vs. Junction Temperature

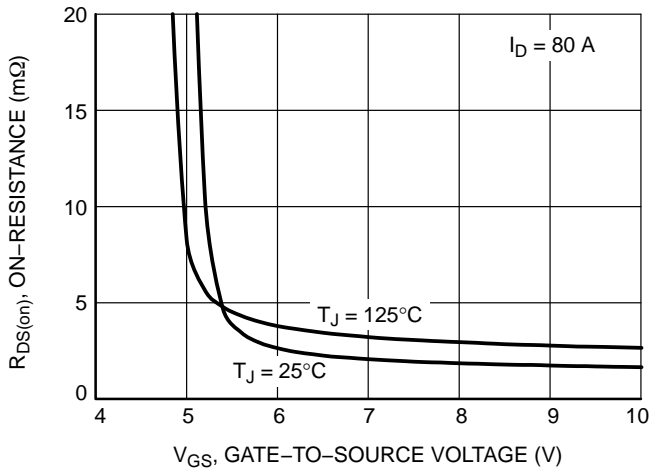


Figure 4. On-Resistance vs. Gate-to-Source Voltage

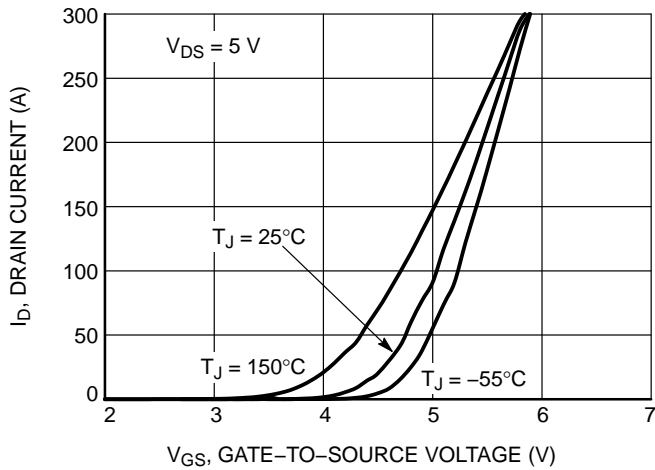


Figure 5. Drain Current vs. Gate-to-Source Voltage

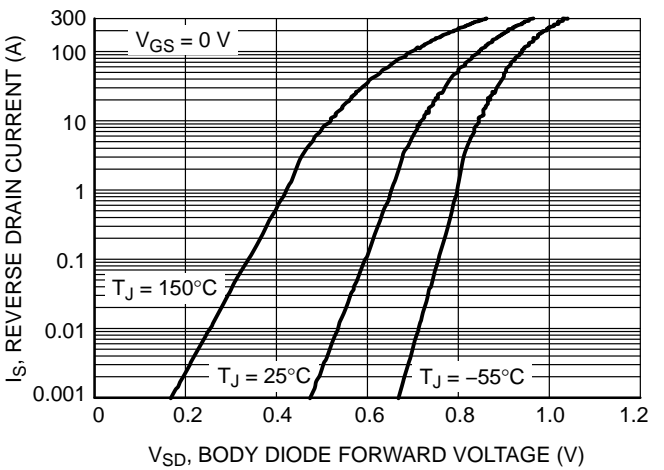


Figure 6. Reverse Drain Current vs. Body Diode Forward Voltage

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TYPICAL CHARACTERISTICS

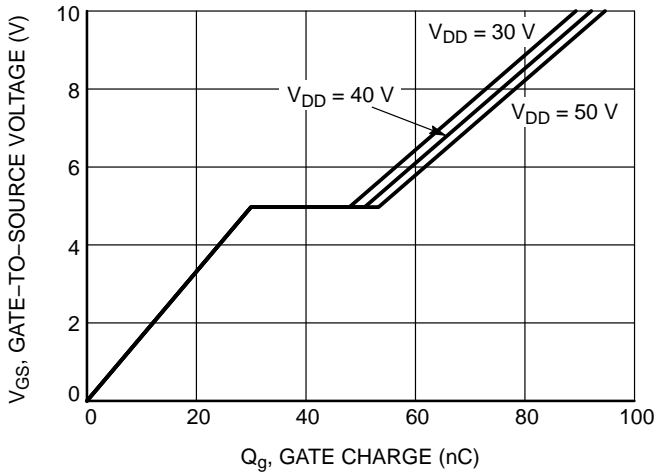


Figure 7. Gate Charge

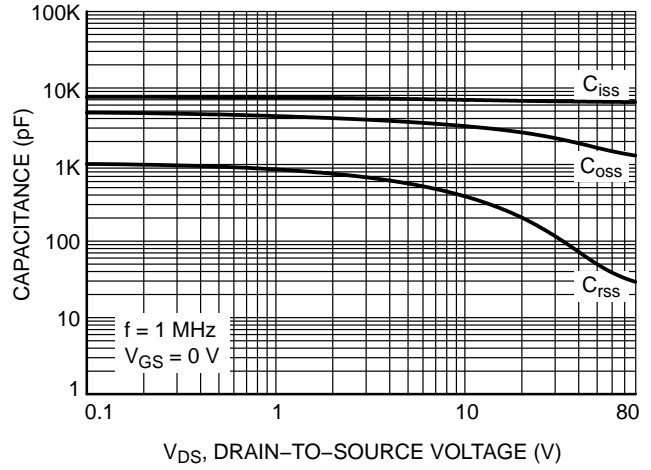


Figure 8. Capacitance Variation

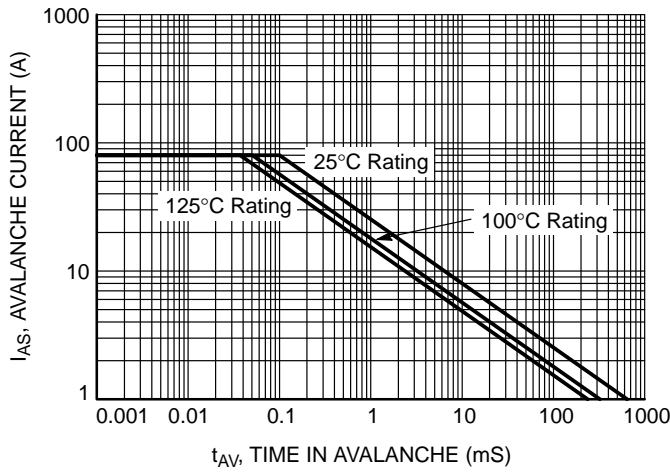


Figure 9. UIL

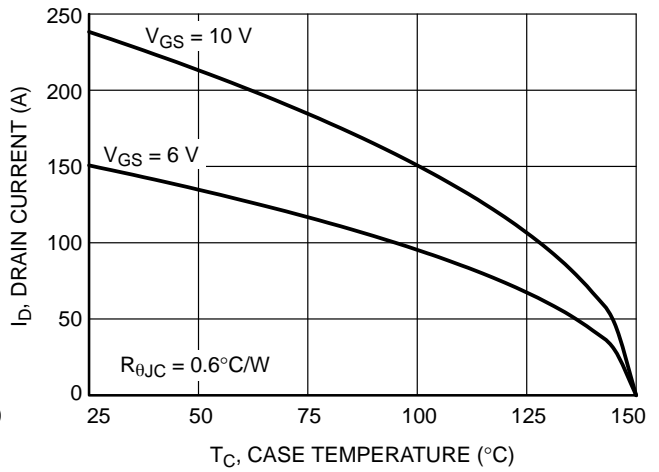


Figure 10. Drain Current vs. Case Temperature

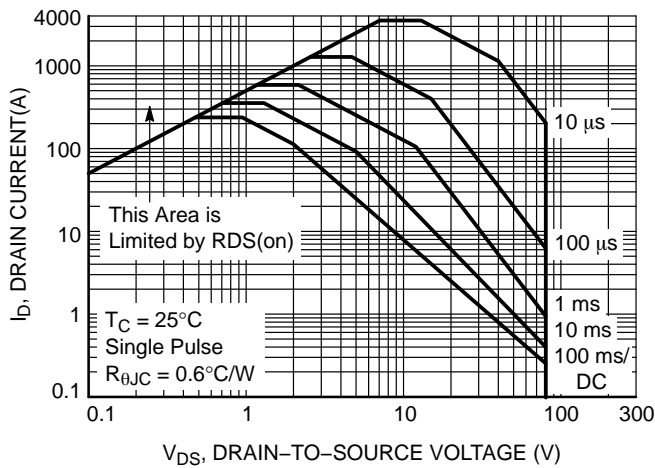


Figure 11. Maximum Rated Forward Biased Safe Operating Area

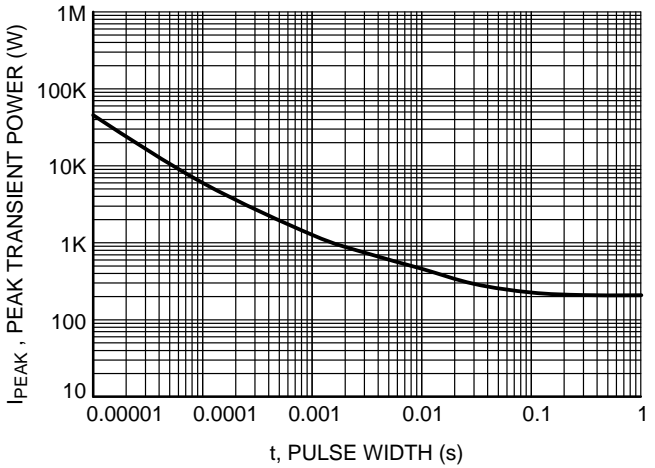


Figure 12. Peak Power

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TYPICAL CHARACTERISTICS

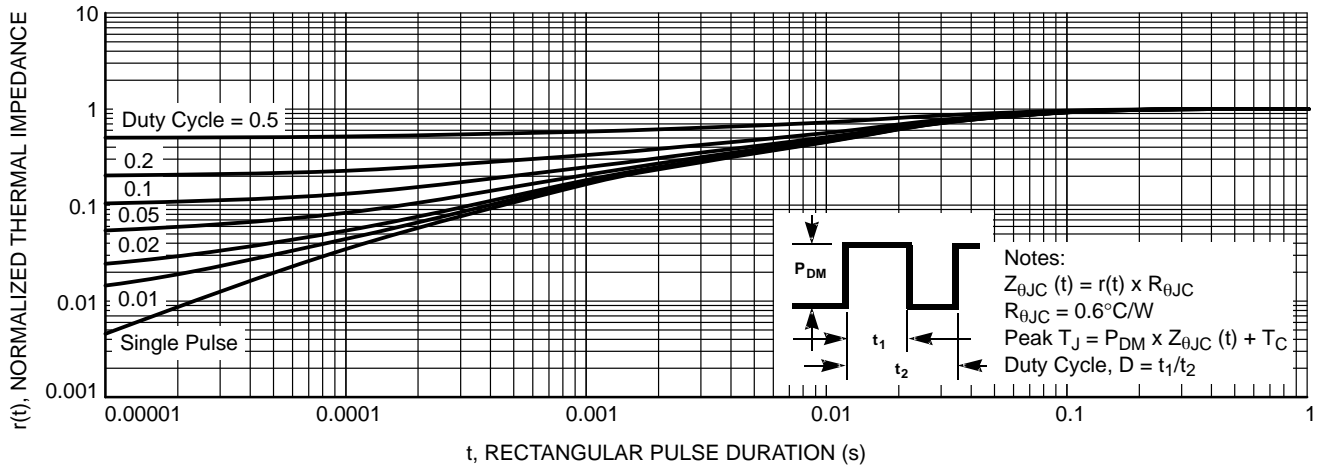


Figure 13. Transient Thermal Impedance

DEVICE ORDERING INFORMATION

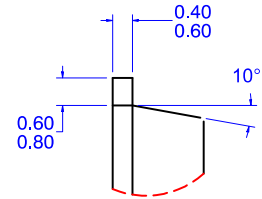
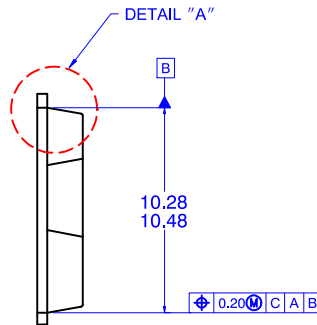
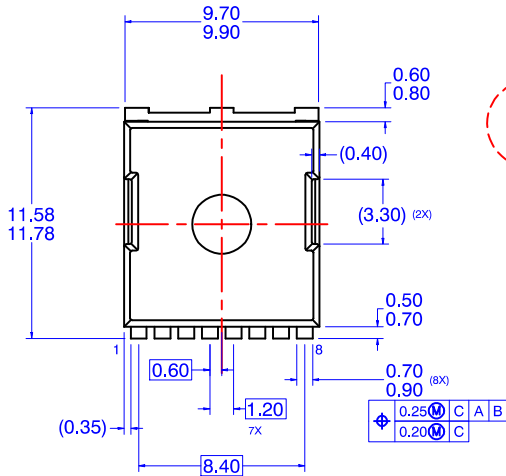
Device	Marking	Package	Shipping†
NTBLS002N08MC	NTBLS 002N08MC	M0-299A (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

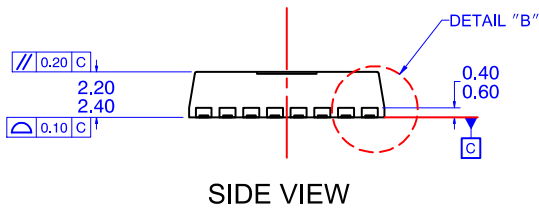
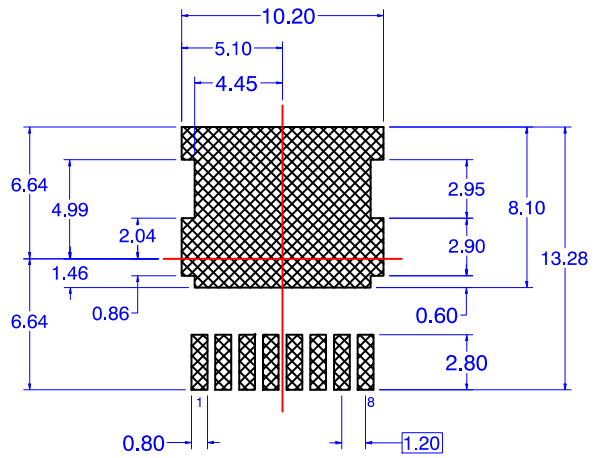
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PACKAGE DIMENSIONS

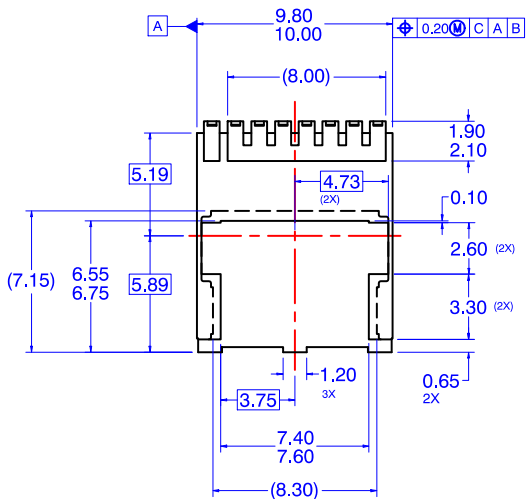
H-PSOF8L 11.68x9.80
CASE 100CU
ISSUE O



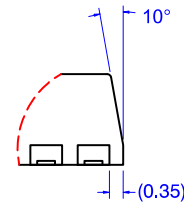
DETAIL "A"



SIDE VIEW




BOTTOM VIEW



DETAIL "B"

- NOTES: UNLESS OTHERWISE SPECIFIED
- PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE A, DATED NOVEMBER 2009.
 - ALL DIMENSIONS ARE IN MILLIMETERS.
 - DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 - DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

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